

Description

The SiT8021 is the industry's smallest and the lowest power MHz oscillator. With 0.1 mW of active power consumption at 3.072 MHz output frequency, this µPower oscillator enables longer battery life for a wearable, IoT or mobile device compared to a quartz-based oscillator or resonator.

The device comes in the smallest 1.5 mm x 0.8 mm package. The unique combination of ultra-low power, ultra-small package and flexible output frequency makes it ideal for power sensitive and space constrained applications.

Applications

- Tablets
- Fitness bands
- Health and medical monitoring
- Wearables
- Portable audio
- Input devices
- IoT devices

Features

- Ultra-low current consumption of 60 µA at 3.072 MHz
- Ultra-small 1.5 mm x 0.8 mm package
- 1 to 26 MHz with 6 decimal places of accuracy
- Operating temperature from -40°C to 85°C
- Frequency stability as low as ±50 ppm
- Programmable output drive strength for best EMI or driving multiple loads
- Ultra-light weight of 1.28 mg
- RoHS and REACH compliant, Pb-free, Halogen-free and Antimony-free





Electrical Specifications

Table 1. Electrical Characteristics

All Min and Max limits are specified over temperature and rated operating voltage with 15 pF output load unless otherwise stated. Typical values are at 25°C and nominal supply voltage.

Parameters	Symbol	Min.	Тур.	Max.	Unit	Condition	
Frequency Range							
Output Frequency Range	f	1.000000		26.000000	MHz		
			Frequenc	y Stability an	nd Aging		
Initial Tolerance	f_tol	-15	ı	+15	ppm	Frequency offset at 25°C post reflow	
Frequency Stability	f_stab	-100	ı	+100	ppm	Inclusive of initial tolerance, and variations over operating temperature -20°C to +70°C or -40°C to +85°C, rated power supply voltage and output load	
		-50	İ	+50	ppm	Inclusive of initial tolerance, and variations over operating temperature -20°C to +70°C, rated power supply voltage and output load	
First Year Aging	f_1year	-3		+3	ppm	at 25°C	
			Operating	g Temperatur	e Range		
Operating Temperature Range T_use -20 - +70 °C Extended Comme		Extended Commercial					
		-40	-	+85	°C	Industrial. Contact SiTime for -40°C to 105°C option.	
		Sup	ply Voltage	and Current	Consumpt	tion	
Supply Voltage	VDD	1.62	1.8	1.98	٧		
		1.62	-	3.63	V	Any voltage from 1.62 to 3.63 V	
Current Consumption ^[1,3]	IDD	_	60	-	μA	f = 3.072 MHz, Vdd = 1.8 V, no load	
		_	110	130	μA	f = 6.144 MHz, Vdd = 1.8 V, no load	
		_	230	270	μA	f = 6.144 MHz, Vdd = 1.8 V, 10 pFload	
		-	-	160	μΑ	f = 6.144 MHz, Vdd = 2.25 V to 3.63 V, no load	
		-	160	-	μA	f = 12 MHz, Vdd = 1.8 V, no load	
Standby Current ^[3]	I_std	_	0.7	1.3	μA	Vdd = 1.8 V, ST pin = HIGH, output is weakly pulled down	
		-	-	1.5	μΑ	Vdd = 1.62 V to 3.63 V, ST pin = HIGH, output is weakly pulled down	



Table 1. Electrical Characteristics (continuous)

Parameters	Symbol	Min.	Тур.	Max.	Unit	Condition	
LVCMOS Output Characteristics							
Duty Cycle	DC	45	ı	55	%		
Rise/Fall Time ^[3]	T_r, T_f	-	4	8	ns	Vdd = 1.8 V, 20% - 80%. Contact SiTime for other programmable rise/fall options	
		-	ı	8	ns	Vdd = 1.62 V to 3.63 V, 20% - 80%. Contact SiTime for other programmable rise/fall options	
Output High Voltage	VOH	90%	-	-	VDD	IOH = -0.5 mA (Vdd = 1.8 V) IOH = -1.2 mA (Vdd = 2.25 V to 3.63 V)	
Output Low Voltage	VOL	-	-	10%	VDD	IOL = 0.5 mA (Vdd = 1.8 V) IOL = 1.2 mA (Vdd = 2.25 V to 3.63 V)	
			Inpu	t Characteris	tics		
Input High Voltage	VIH	80%	_	_	VDD		
Input Low Voltage	VIL	-	_	20%	VDD		
Input Slew Rate	In-slew	10	ı	ı	V/µs		
Input Pull-down Impedance	Z_in	300	ı	ı	kΩ	Active mode (ST pin = LOW), Vdd = 1.8 V	
		270	ı	ı	kΩ	Active mode (ST pin = LOW), Vdd = 2.25 V to 3.63 V	
		2.5	ı	ı	ΜΩ	Standby mode (ST pin = HIGH), Vdd = 1.8 V	
		1.3	ı	ı	ΜΩ	Standby mode (ST pin = HIGH), Vdd = 2.25 V to 3.63 V	
	Startup, Standby and Resume Timing						
Startup Time	T_start	1	75	150	ms	Measured from the time VDD reaches 90% of its final value	
Standby Time	T_stdby	-	Ī	20	μs	Measured from the time ST pin crosses 50% threshold	
Resume Time	T_resume	_	2	3	ms	Measured from the time ST pin crosses 50% threshold	
	Jitter						
RMS Period Jitter ^[3]	T_jitt	-	75	110	ps	f = 6.144 MHz, Vdd = 1.8 V	
		_	-	110	ps	f = 6.144 MHz, Vdd = 2.25 V to 3.63 V	
RMS Phase Jitter ^[3]	T_phj	_	0.8	2.5	ns	f = 6.144 MHz, Vdd = 1.8 V, Integration bandwidth = 100 Hz to 40 kHz ^[2]	
		-	-	2.5	ns	f = 6.144 MHz, Vdd = 2.25 V to 3.63 V, Integration bandwidth = 100 Hz to 40 kHz ^[2]	

Notes:

- Current consumption with load is a function of the output frequency and output load. For any given output frequency, the capacitive loading will increase current consumption equal to C_load*VDD*f(MHz).
- 2. Max spec inclusive of 25 mV peak-to-peak sinusoidal noise on VDD. Noise frequency 100 Hz to 20 MHz.
- 3. Refer to the performance plot section for typical values at 2.5, 2.8, 3.0 and 3.3 V condition

Table 2. Pin Description

Pin	Symbol	Functionality			
1	ST	Input	L: Specified frequency output H: Output is low (weak pull down). Device goes to the standby mode. Supply current reduces to I_std.		
2	OUT	Output	Output LVCMOS clock output		
3	VDD	Power	Supply voltage. Bypass with a 0.01 µF X7R capacitor.		
4	GND	Power	Connect to ground		

Top View

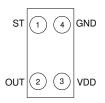


Figure 1. Pin Assignments



Table 3. Absolute Maximum Limits

Attempted operation outside the absolute maximum ratings may cause permanent damage to the part. Actual performance of the IC is only guaranteed within the operational specifications, not at absolute maximum ratings.

Parameter	Test Condition	Value	Unit
Continuous Power Supply Voltage Range (VDD)		-0.5 to 3.63	V
Short Duration Maximum Power Supply Voltage (VDD)	<30 seconds	4.0	V
Continuous Maximum Operating Temperature		105	°C
Short Duration Maximum Operating Temperature	≤30 seconds	125	°C
Human Body Model (HBM) ESD Protection	JESD22-A115	2000	V
Charge-Device Model (CDM) ESD Protection	JESD22-C101	750	V
Machine Model (MM) ESD Protection	T _A = 25°C	200	V
Latch-up Tolerance	JESD:	78 Compliant	
Mechanical Shock Resistance	MII 883, Method 2002	10,000	g
Mechanical Vibration Resistance	MII 883, Method 2007	70	g
1508 CSP Junction Temperature		150	°C
Storage Temperature		-65 to 150	°C
Soldering Temperature (follow standard Pb free soldering guidelines)	-	260	°C



Block Diagram

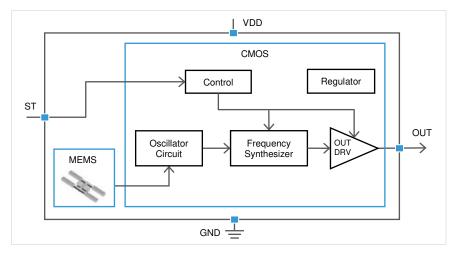


Figure 2. SiT8021 Block Diagram

Device Operating Modes and Outputs

The SiT8021 supports a $\leq 0.7 \, \mu A$ standby mode for battery-powered and other power sensitive applications. The switching between the active and standby modes is controlled by the logic level on the ST pin as shown in the table below.

Table 4. Operating Modes and Output States

ST Pin	MODE	OUTPUT	IDD Example	
LOW	Active	Specified frequency	60 μA @ 3.072 MHz	
FLOAT	Active with 200 kΩ internal pull-down	Specified frequency	60 μA @ 3.072 MHz	
HIGH	Standby	Hi-Z, pulled-down with 1 MΩ impedence	1.3 μΑ	

Active Mode

The SiT8021 operates in the active mode when the ST pin is at logic LOW or FLOAT. In the active mode, the device uses the on-chip frequency synthesizer to generate an output from the internal MEMS resonator reference. The frequency of the output is factory programmed based on the device ordering code.

Standby Mode

The SiT8021 operates in the standby mode when the ST pin is at logic HIGH. In the standby mode, all internal circuits with the exception of the MEMS oscillator circuit and the ST pin detection logic are turned off to reduce power consumption. While in standby mode, the input impedance of the ST pin is increased to further reduce system-level power consumption.

The output driver of the device in the standby mode is pulled-down with 1 $\ensuremath{M\Omega}$ impedance.

Output During Startup and Resume

The SiT8021 starts up with the output disabled. The output is enabled once all internal circuit blocks are active, and logic LOW or FLOAT is detected on the ST pin.

As shown in Table 4, logic HIGH at the ST pin forces the SiT8021 into the "standby" state, causing the output to disable. Upon pulling the ST pin LOW, the device enters the "resume" state, keeping the output disabled. Once the "resume" state ends, the device output enables.

The first clock pulse after startup or resume is accurate to the rated stability.

Low Power Design Guidelines

For high EM noise environments, we recommend the following design guidelines:

- Place oscillator as far away from EM noise sources as possible (e.g., high-voltage switching regulators, motor drive control).
- Route noisy PCB traces, such as digital data lines or high di/dt power supply lines, away from the SiTime oscillator.
- Place a solid GND plane underneath the SiTime oscillator to shield the oscillator from noisy traces on the other board layers.

Manufacturing Guidelines

- No Ultrasonic or Megasonic Cleaning: Do not subject the SiT8021 to an ultrasonic or megasonic cleaning environment. Permanent damage or long-term reliability issues to the device may occur in such an event.
- Applying board-level underfill (BLUF) to the device is acceptable, but will cause a slight shift of few ppm in the initial frequency tolerance. Tested with UF3810, UF3808, and FP4530 underfill.
- Reflow profile, per JESD22-A113D.

For additional manufacturing guidelines and marking/tape-reel instructions, refer to SiTime Manufacturing Notes.



Test Circuit and Waveform

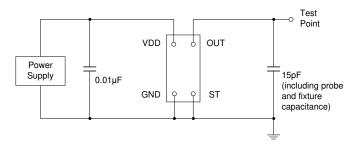


Figure 3. Test Circuit

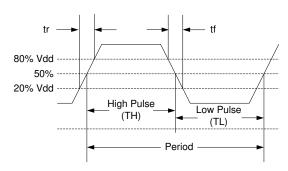
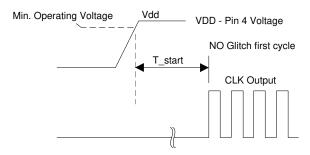


Figure 4. Waveform^[4]

Note:

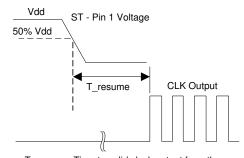
4. Duty Cycle is computed as Duty Cycle = TH/Period.

Timing Diagram



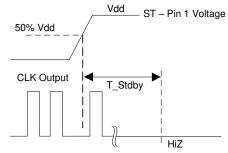
T_start: Time to valid clock output from power on

Figure 5. Startup Timing^[5,6]



T_resume: Time to valid clock output from the time ST pin crosses 50% threshold

Figure 6. Resume Timing^[5,6]



T_Stdby: Time for output to go high-Z from the time ST pin crosses 50% threshold

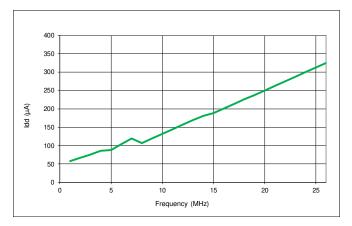
Figure 7. Standby Timing^[5]

Notes:

- 5. SiT8021 supports "no runt" pulses and "no glitch" output during startup or resume.
- 6. SiT8021 supports gated output which is accurate within rated frequency stability from the first cycle.



Performance Plots[7]



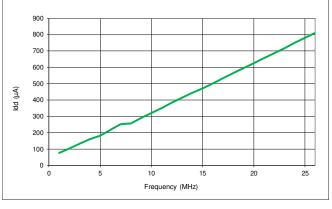
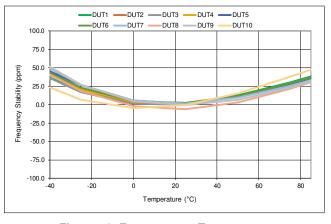


Figure 8. Idd vs Frequency without load

Figure 9. Idd vs Frequency with 10 pF load



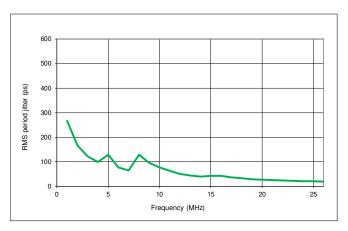
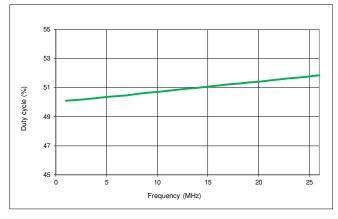


Figure 10. Frequency vs Temperature

Figure 11. RMS Period Jitter vs Frequency



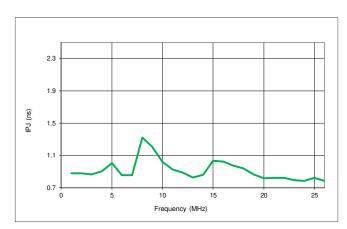
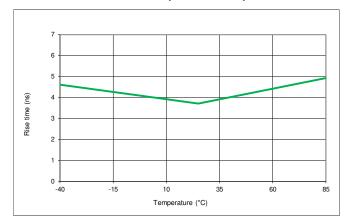


Figure 12. Duty Cycle vs Frequency

Figure 13. RMS Phase Jitter Random vs Frequency^[8]



Performance Plots[7] (continuous)



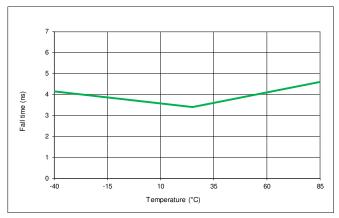


Figure 14. Rise Time vs Temperature^[9]

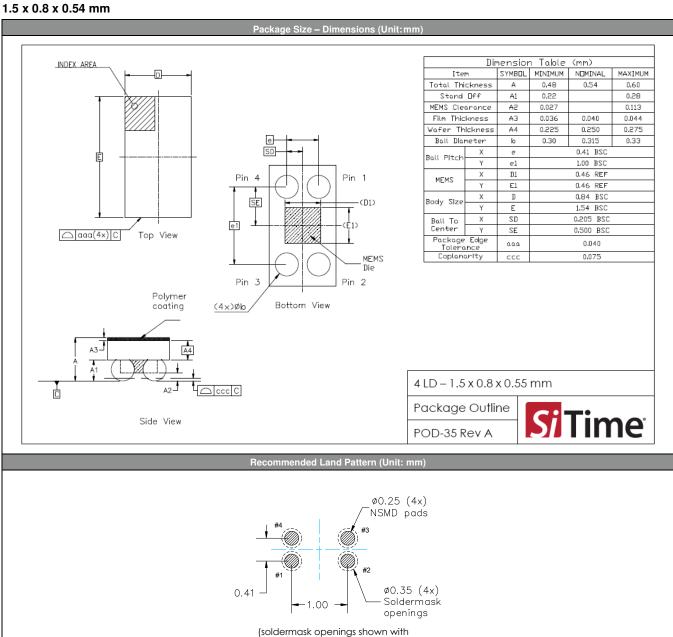
Figure 15. Fall Time vs Temperature^[9]

Notes:

- 7. All data is measured at room temperature, unless otherwise stated.
- 8. Integration range is from 100 Hz to 40 kHz.9. Data is measured with 15 pF load.



Dimensions and Patterns

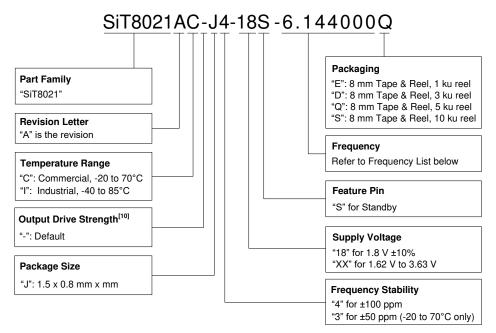


dashed line around NSMD pad)

Recommended 4-mil (0.1mm) stencil thickness



Ordering Information



Notes:

10. Contact SiTime for other drive strength options that result in different rise/fall time for any given output load.

Table 5. List of Standard Frequencies[11]

2.048 MHz	4 MHz	6.144 MHz	8 MHz	12 MHz	12.288 MHz	16 MHz
19.2 MHz	24 MHz	26 MHz				

Notes:

11. All frequencies from 1 to 26 MHz are in production. Contact SiTime for minimum order quantity requirement.



Table 6. Revision History

Version	Release Date	Change Summary
0.1	15-Dec-2014	Advance Information
0.2	27-Jan-2015	Updated CSP dimension tolerance
		Removed 2.0 mm x 1.6 mm package
		Changed to 6.144 MHz as the reference frequency for jitter, IDD and other relevant parameters
		Changed resume time (max) to 5 ms
		Changed the parameter PSNR to Power Supply Noise Sensitivity and specified in RMS
0.3	31-Mar-2015	Changed VIL and VIH values in the EC table
		Reduced standby time in the EC table
		Revised phase jitter condition to include power supply noise sensitivity
		Removed power supply noise spec
0.9	22-May-2015	Added typical values for active and standby current
		Added current consumption for additional frequencies
		Changed ±50 ppm option to Contact SiTime
		Added manufacturing guideline
		Other miscellaneous format and footnote changes
1.0	18-Nov-2015	Revised initial tolerance, current consumption, standby current, input high/low voltage, input pull-down impedance,
		startup/resume time and RMS period/phase jitter in Table 1
1.1	19-Feb-2016	Added performance plots
		Added 10 Standard frequencies to the ordering information
1.11	16-Sep-2016	Updated the table.5 list of standard frequencies
		Added a graph of Idd vs Frequency without load to the performance plots section
1.2	28-Sep-2017	Added 2.25 to 3.63 V supply voltage option Updated logo and company address, other page layout changes
		Added package dimension table to the dimensions and patterns section
1.0	40 Nov. 0000	
1.3	18-Nov-2020	Added ±50 ppm frequency stability option Formatting, rev table date format and TempFlat MEMS logo update
1.31	29-Mar-2021	Added Q-suffix to the Ordering table options
1.00	04.4 0000	Updated hyperlinks, changed date format
1.32	21-Apr-2022	Expanded Continuous Voltage range from 1.62V (lowered). Updated Ordering Information

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